



BYV32E-100

Dual rugged ultrafast rectifier diode, 20 A, 100 V

Rev.05 - 7 March 2018

Product data sheet

1. General description

Ultrafast dual epitaxial rectifier diode in a SOT78 (TO-220AB) plastic package.

2. Features and benefits

- High reverse voltage surge capability
- High thermal cycling performance
- Low thermal resistance
- Very low on-state loss
- Soft recovery characteristic minimizes power consuming oscillations

3. Applications

- Output rectifiers in high-frequency switched-mode power supplies

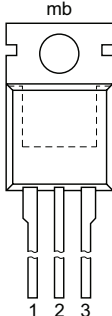
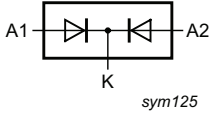
4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit
Absolute maximum rating						
V_{RRM}	repetitive peak reverse voltage		100			V
$I_{O(AV)}$	average output current	$\delta = 0.5$; square-wave pulse; $T_{mb} \leq 115\text{ °C}$; both diodes conducting; Fig. 1 ; Fig. 2	20			A
I_{RRM}	repetitive peak reverse current	$\delta = 0.001$; $t_p = 2\ \mu\text{s}$;	0.2			A
V_{ESD}	electrostatic discharge voltage	HBM; $C = 250\ \text{pF}$; $R = 1.5\ \text{k}\Omega$; all pins	8			kV
I_{FRM}	repetitive peak forward current	$\delta = 0.5$; $t_p = 25\ \mu\text{s}$; $T_{mb} \leq 115\text{ °C}$; per diode	20			A
I_{FSM}	non-repetitive peak forward current	$t_p = 10\ \text{ms}$; sine-wave pulse; $T_{j(\text{init})} = 25\text{ °C}$; per diode	125			A
		$t_p = 8.3\ \text{ms}$; sine-wave pulse; $T_{j(\text{init})} = 25\text{ °C}$; per diode	137			A
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V_F	forward voltage	$I_F = 8\ \text{A}$; $T_j = 150\text{ °C}$; Fig. 4	-	0.72	0.85	V
Dynamic characteristics						
t_{rr}	reverse recovery time	$I_F = 1\ \text{A}$; $V_R = 30\ \text{V}$; $di_F/dt = 100\ \text{A}/\mu\text{s}$; $T_j = 25\text{ °C}$; ramp recovery; Fig. 5	-	20	25	ns
		$I_F = 0.5\ \text{A}$ to $I_R = 1\ \text{A}$; $T_j = 25\text{ °C}$; measured at $I_R = 0.25\ \text{A}$; step recovery; Fig. 6	-	10	20	ns

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1		
2	K	cathode		
3	A2	anode 2		
mb	K	mounting base; cathode		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BYV32E-100	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

7. Marking

Table 4. Marking codes

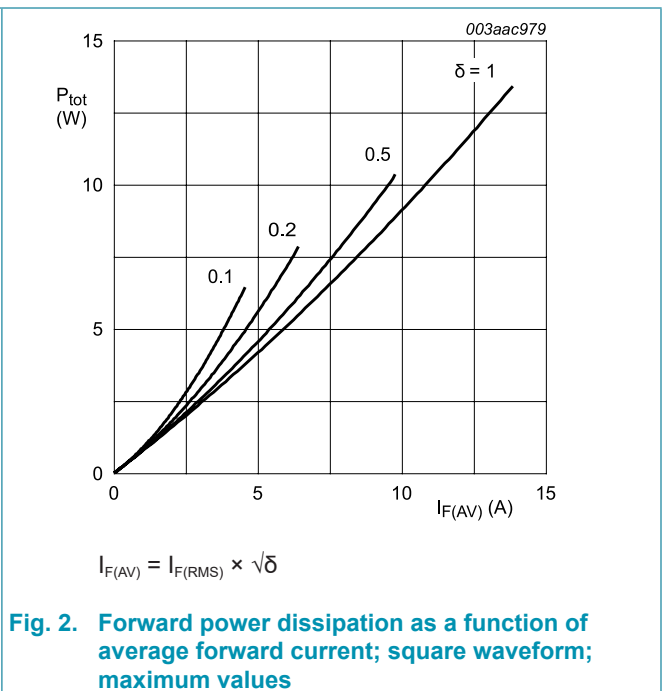
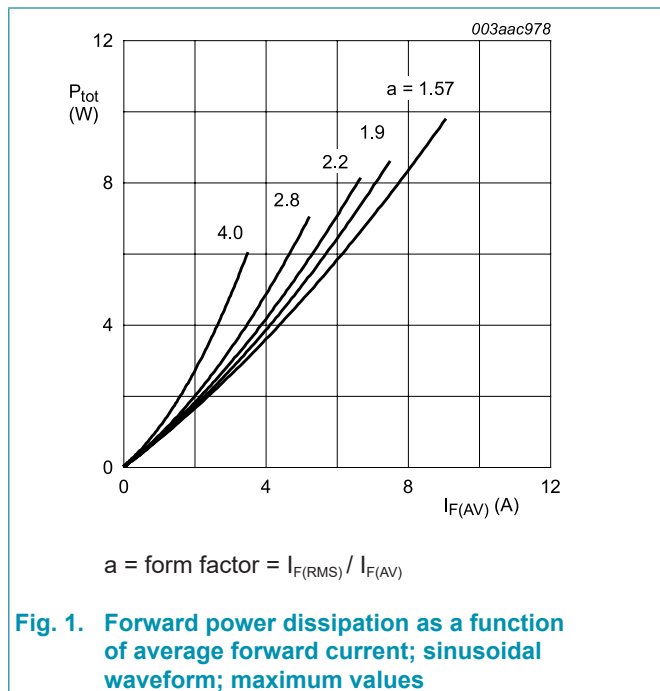
Type number	Marking codes
BYV32E-100	BYV32E-100

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		100	V
V_{RWM}	crest working reverse voltage		100	V
V_R	reverse voltage	DC	100	V
$I_{O(AV)}$	average output current	$\delta = 0.5$; square-wave pulse; $T_{mb} \leq 115\text{ }^\circ\text{C}$; both diodes conducting; Fig 1; Fig 2	20	A
I_{FRM}	repetitive peak forward current	$\delta = 0.5$; $t_p = 25\text{ }\mu\text{s}$; $T_{mb} \leq 115\text{ }^\circ\text{C}$; per diode	20	A
I_{FSM}	non-repetitive peak forward current	$t_p = 10\text{ ms}$; sine-wave pulse; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$; per diode	125	A
		$t_p = 8.3\text{ ms}$; sine-wave pulse; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$; per diode	137	A
I_{RRM}	repetitive peak reverse current	$\delta = 0.001$; $t_p = 2\text{ }\mu\text{s}$; per diode	0.2	A
I_{RSM}	non-repetitive peak reverse current	$t_p = 100\text{ }\mu\text{s}$; per diode	0.2	A
T_{stg}	storage temperature		-40 to 150	$^\circ\text{C}$
T_j	junction temperature		150	$^\circ\text{C}$
V_{ESD}	electrostatic discharge voltage	HBM; all pins; C = 250 pF; R = 1.5 k Ω	8	kV



9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	with heatsink compound; both diodes conducting	-	-	1.6	K/W
		with heatsink compound; per diode; Fig 3	-	-	2.4	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient		-	60	-	K/W

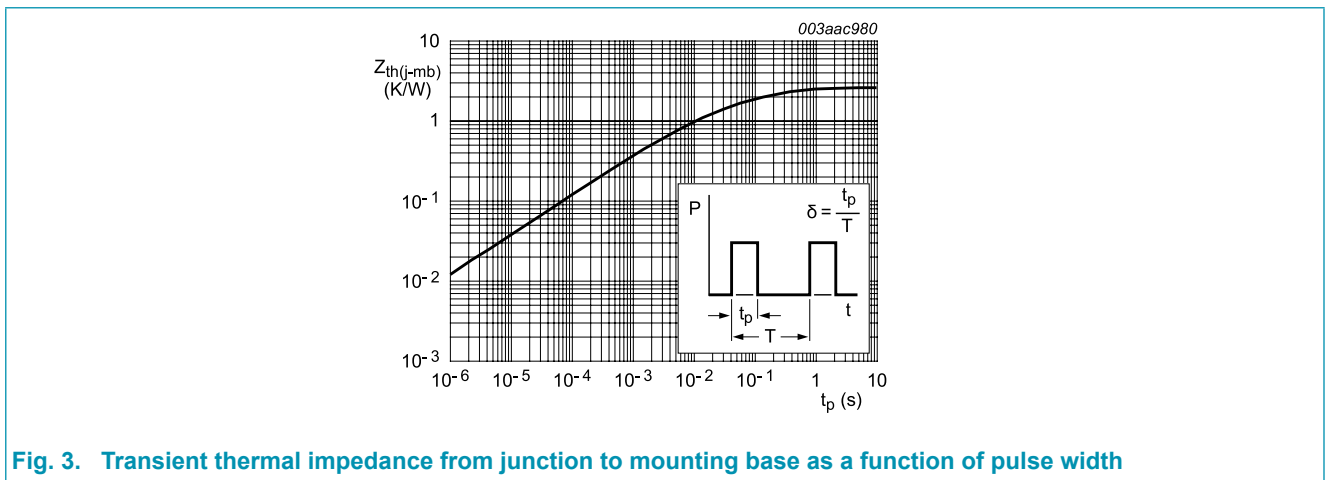
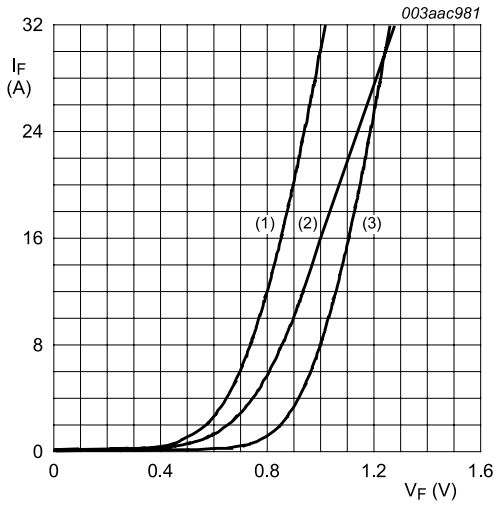


Fig. 3. Transient thermal impedance from junction to mounting base as a function of pulse width

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V_F	forward voltage	$I_F = 8 \text{ A}; T_j = 150 \text{ }^\circ\text{C};$ Fig. 4	-	0.72	0.85	V
		$I_F = 20 \text{ A}; T_j = 25 \text{ }^\circ\text{C}$	-	1	1.15	V
I_R	reverse current	$V_R = 100 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	6	30	μA
		$V_R = 100 \text{ V}; T_j = 100 \text{ }^\circ\text{C}$	-	0.2	0.6	mA
Dynamic characteristics						
Q_r	recovered charge	$I_F = 2 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 20 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ }^\circ\text{C}$	-	8	12.5	nC
t_{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ }^\circ\text{C};$ ramp recovery; Fig. 5	-	20	25	ns
		$I_F = 0.5 \text{ A to } I_R = 1 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ measured at $I_R = 0.25 \text{ A};$ step recovery; Fig. 6	-	10	20	ns
V_{FR}	forward recovery voltage	$I_F = 1 \text{ A}; dI_F/dt = 10 \text{ A}/\mu\text{s}; T_j = 25 \text{ }^\circ\text{C};$ Fig. 7	-	-	1	V



- (1) $T_j = 150\text{ }^\circ\text{C}$; typical values
- (2) $T_j = 150\text{ }^\circ\text{C}$; maximum values
- (3) $T_j = 25\text{ }^\circ\text{C}$; maximum values

Fig. 4. Forward current as a function of forward voltage

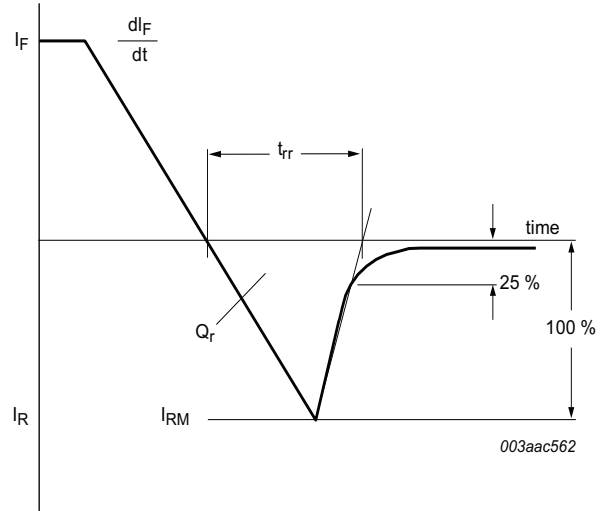


Fig. 5. Reverse recovery definitions; ramp recovery

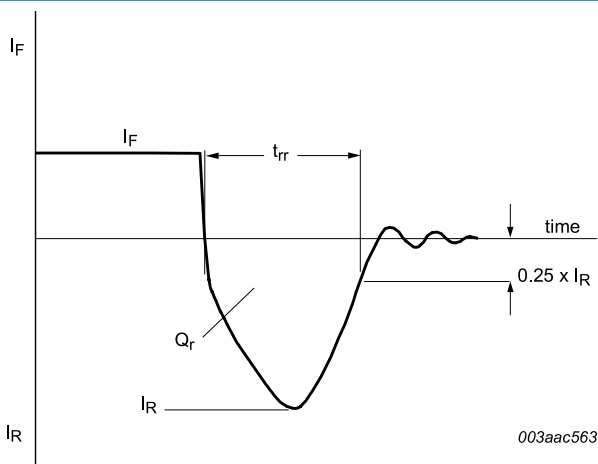


Fig. 6. Reverse recovery definitions; step recovery

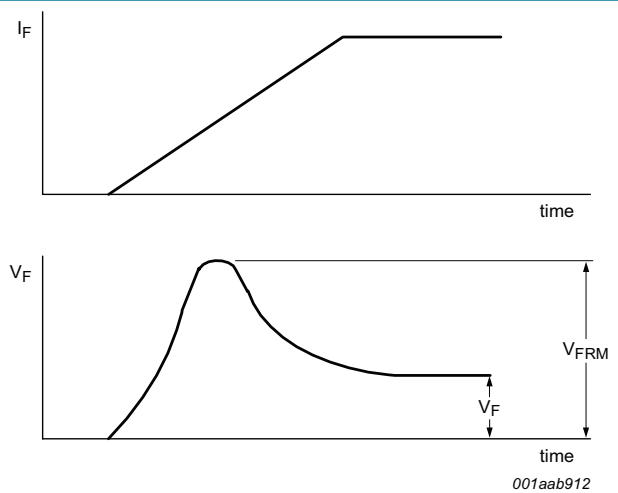
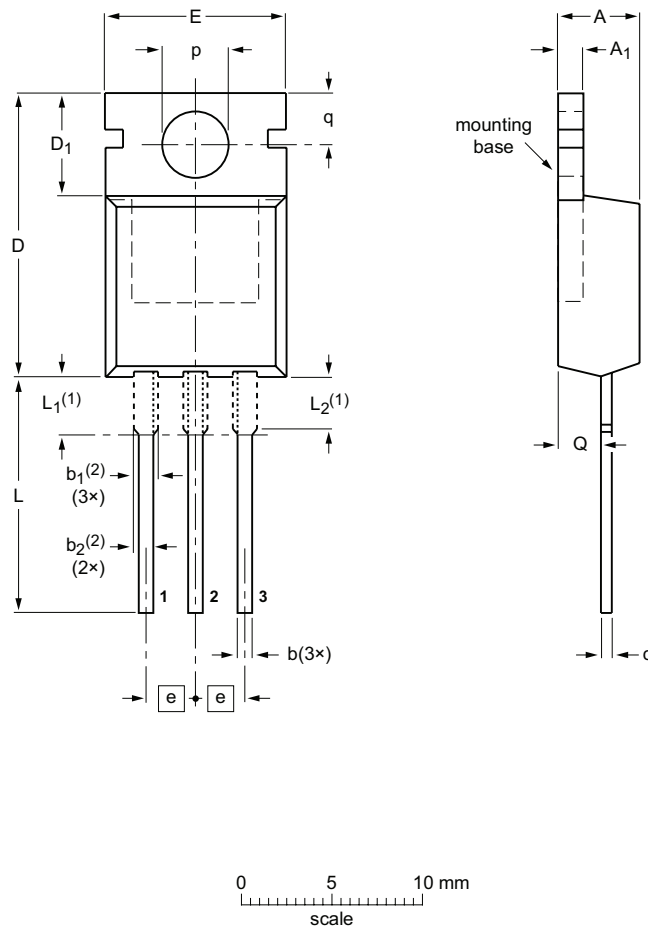


Fig. 7. Forward recovery definitions

11. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b	b ₁ (2)	b ₂ (2)	c	D	D ₁	E	e	L	L ₁ (1)	L ₂ (1) max.	p	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

1. Lead shoulder designs may vary.
2. Dimension includes excess dambar.

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13

12. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BYV32E-100 v.5	20180307	Product specification	-	BYV32E-100_4
Modifications:	Change from NXP version to WeEn version			
BYV32E-100_4	20090302	Product specification	-	BYV32E_SERIES_3
Modifications:	<ul style="list-style-type: none"> The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. Legal texts have been adapted to the new company name where appropriate. Package outline updated. Type number BYV32E-100 separated from data sheet BYV32E_SERIES_3 			
BYV32E_SERIES_3	20010301	Product specification	-	BYV32E_SERIES_2
BYV32E_SERIES_2	19980701	Product specification	-	BYV32EB_SERIES_1
BYV32EB_SERIES_1	19960801	Product specification	-	-

13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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